

100-Pin TQFP
Commercial Temp
Industrial Temp

512K x 18, 256K x 32, 256K x 36
8Mb Sync Burst SRAMs

100 MHz 66 MHz
3.3 V V_{DD}
3.3 V and 2.5 V I/O

Features

- \overline{FT} pin for user-configurable flow through or pipelined operation
- Dual Cycle Deselect (DCD) operation
- 3.3 V +10%/−5% core power supply
- 2.5 V or 3.3 V I/O supply
- \overline{LBO} pin for Linear or Interleaved Burst mode
- Internal input resistors on mode pins allow floating mode pins
- Default to Interleaved Pipeline mode
- Byte Write (\overline{BW}) and/or Global Write (\overline{GW}) operation
- Common data inputs and data outputs
- Clock Control, registered, address, data, and control
- Internal self-timed write cycle
- Automatic power-down for portable applications
- 100-lead TQFP package

| | | -11 | -11.5 | -100 | -80 | -66 |
|----------|-----------------|--------|---------|--------|---------|--------|
| Pipeline | tCycle | 10 ns | 10 ns | 10 ns | 12.5 ns | 15 ns |
| 3-1-1-1 | t _{KQ} | 4.0 ns | 4.0 ns | 4.0 ns | 4.5 ns | 5.0 ns |
| | I _{DD} | 225 mA | 225 mA | 225 mA | 200 mA | 185 mA |
| Flow | t _{KQ} | 11 ns | 11.5 ns | 12 ns | 14 ns | 18 ns |
| Through | tCycle | 15 ns | 15 ns | 15 ns | 15 ns | 20 ns |
| | I _{DD} | 180 mA | 180 mA | 180 mA | 175 mA | 165 mA |

Functional Description

Applications

The GS880E18/32/36T is a 9,437,184-bit (8,388,608-bit for x32 version) high performance synchronous SRAM with a 2-bit burst address counter. Although of a type originally developed for Level 2 Cache applications supporting high performance CPUs, the device now finds application in synchronous SRAM applications, ranging from DSP main store to networking chip set support.

Controls

Addresses, data I/Os, chip enables ($\overline{E1}$, $\overline{E2}$, $\overline{E3}$), address burst control inputs (\overline{ADSP} , \overline{ADSC} , \overline{ADV}) and write control inputs (\overline{Bx} , \overline{BW} , \overline{GW}) are synchronous and are controlled by a positive-edge-triggered clock input (CK). Output enable (\overline{G}) and power down control (ZZ) are asynchronous inputs. Burst cycles can be initiated with either \overline{ADSP} or \overline{ADSC} inputs. In Burst mode, subsequent burst addresses are generated internally and are controlled by \overline{ADV} . The burst address counter may be configured to count in either linear or

interleave order with the Linear Burst Order (\overline{LBO}) input. The Burst function need not be used. New addresses can be loaded on every cycle with no degradation of chip performance.

Flow Through / Pipeline Reads

The function of the Data Output register can be controlled by the user via the \overline{FT} mode pin (Pin 14). Holding the \overline{FT} mode pin low places the RAM in Flow Through mode, causing output data to bypass the Data Output Register. Holding \overline{FT} high places the RAM in Pipeline mode, activating the rising-edge-triggered Data Output Register.

DCD Pipelined Reads

The GS880E18/32/36T is a DCD (Dual Cycle Deselect) pipelined synchronous SRAM. SCD (Single Cycle Deselect) versions are also available. DCD SRAMs pipeline disable commands to the same degree as read commands. DCD RAMs hold the deselect command for one full cycle and then begin turning off their outputs just after the second rising edge of clock.

Byte Write and Global Write

Byte write operation is performed by using Byte Write enable (\overline{BW}) input combined with one or more individual byte write signals (\overline{Bx}). In addition, Global Write (\overline{GW}) is available for writing all bytes at one time, regardless of the byte write control inputs.

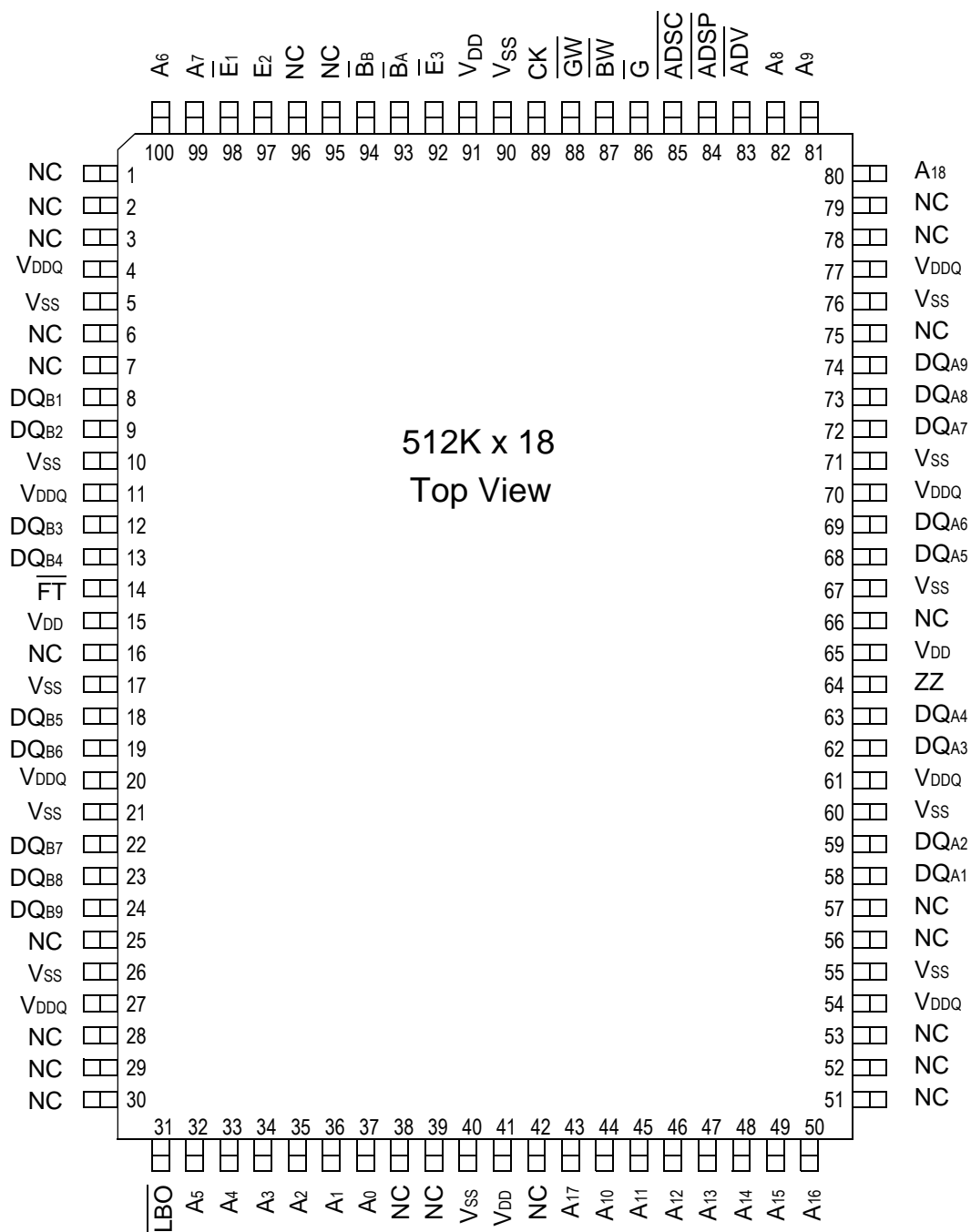
Sleep Mode

Low power (Sleep mode) is attained through the assertion (high) of the ZZ signal, or by stopping the clock (CK). Memory data is retained during Sleep mode.

Core and Interface Voltages

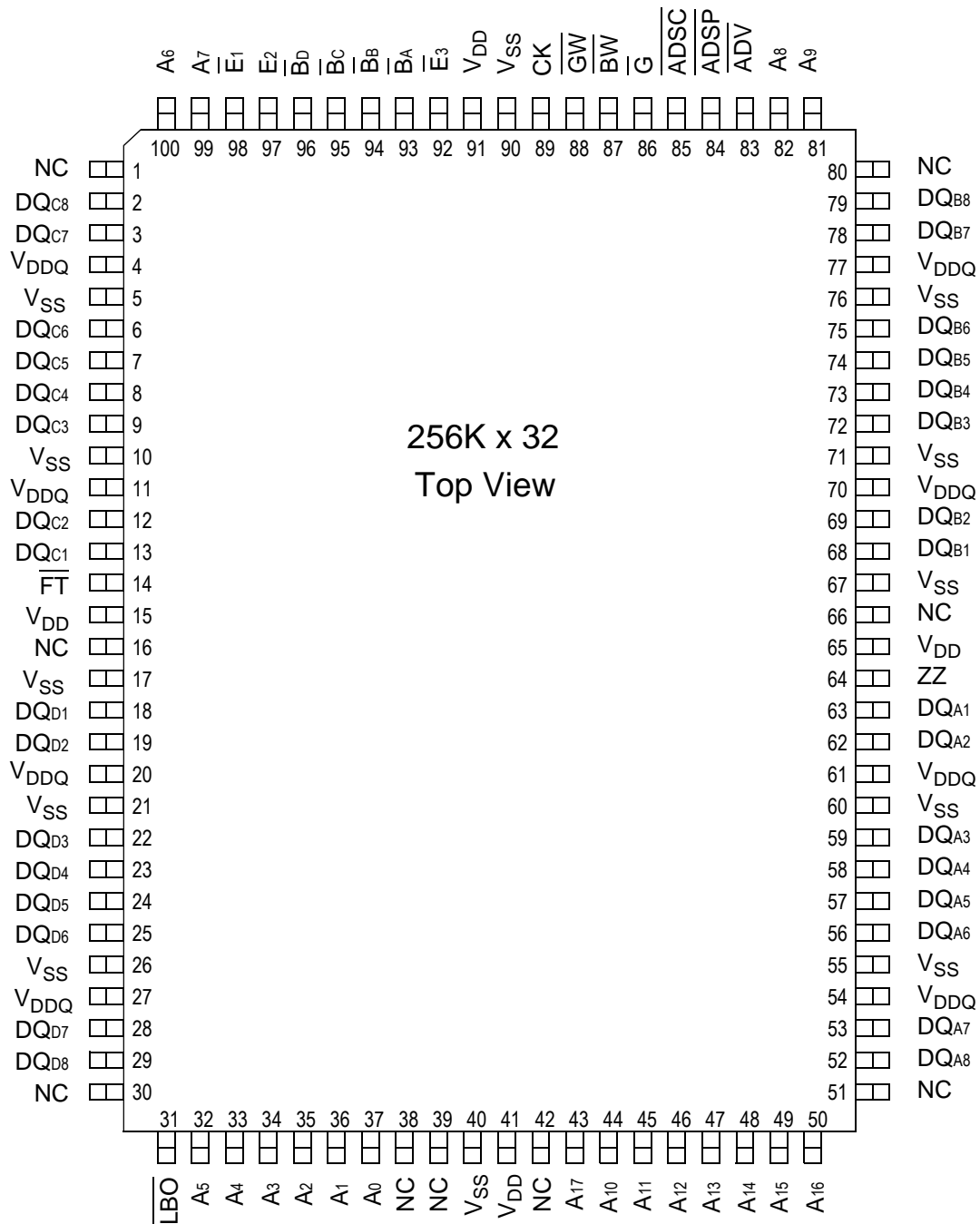
The GS880E18/32/36T operates on a 3.3 V power supply, and all inputs/outputs are 3.3 V- and 2.5 V-compatible. Separate output power (V_{DDQ}) pins are used to decouple output noise from the internal circuit.

GS880E18 100-Pin TQFP Pinout

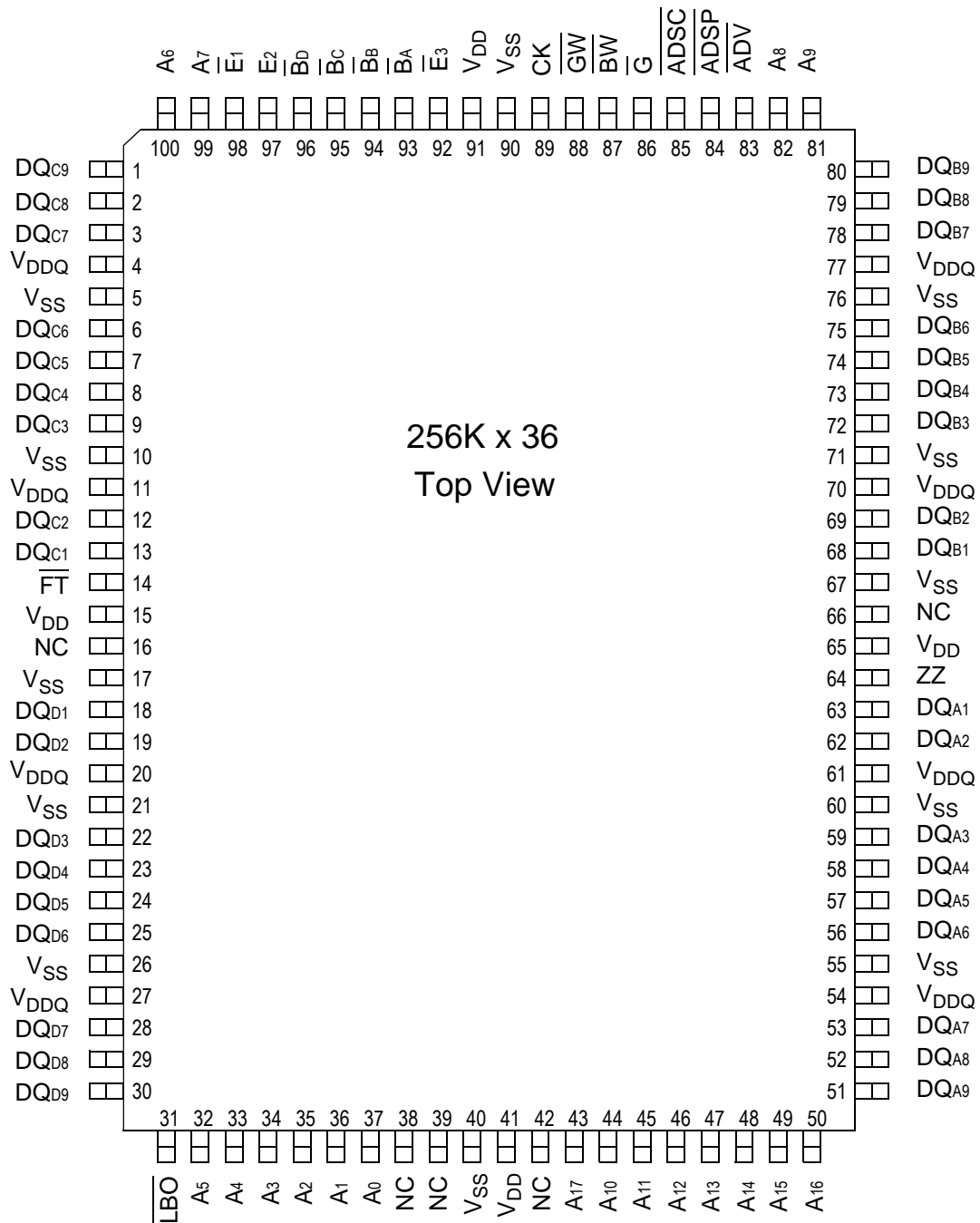


**512K x 18
 Top View**

GS880E32 100-Pin TQFP Pinout



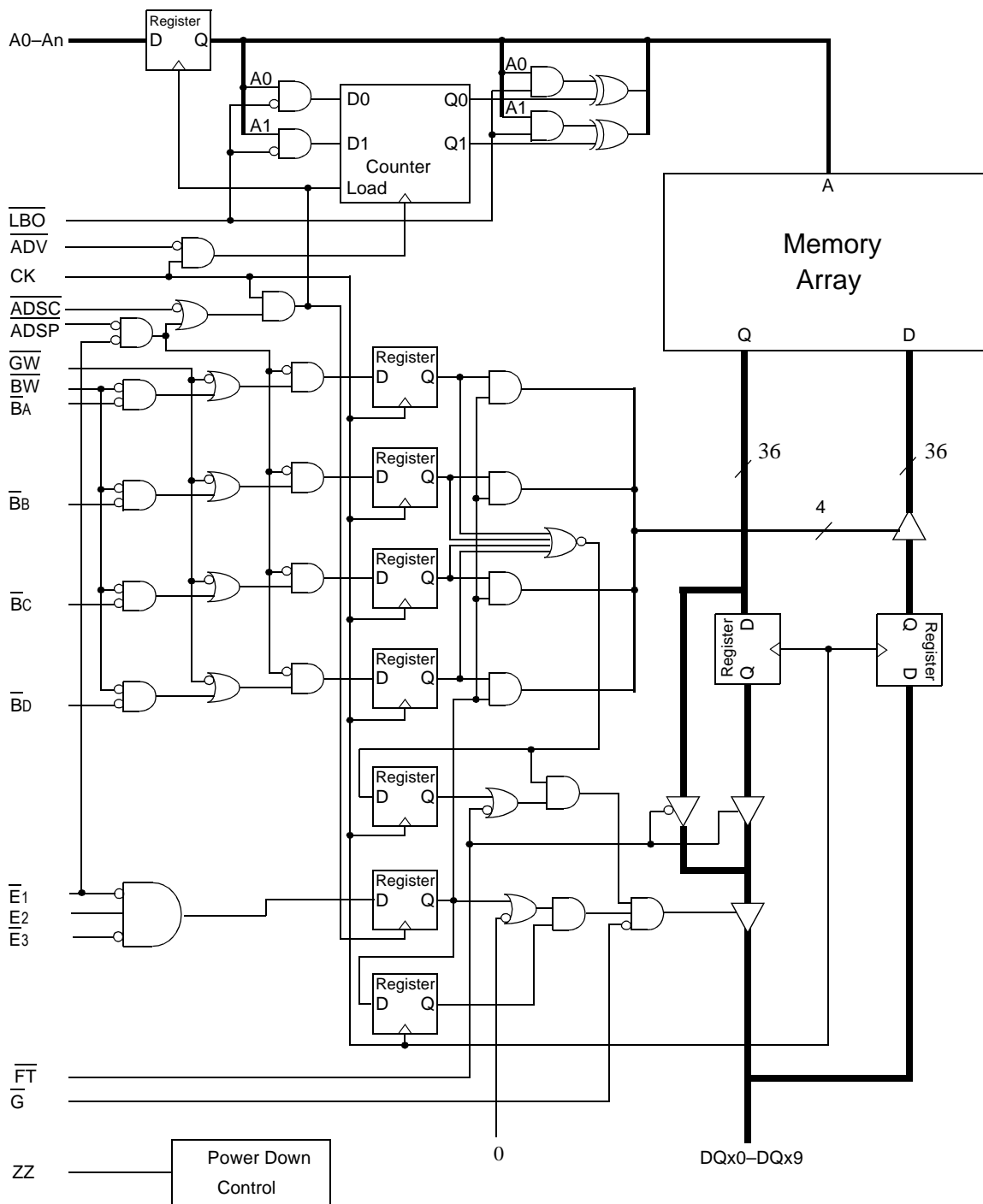
GS880E36 100-Pin TQFP Pinout



TQFP Pin Description

| Pin Location | Symbol | Type | Description |
|--|--|------|---|
| 37, 36 | A ₀ , A ₁ | I | Address field LSBs and Address Counter preset Inputs |
| 35, 34, 33, 32, 100, 99, 82, 81, 44, 45, 46, 47, 48, 49, 50, 43 | A ₂ A ₁₇ | I | Address Inputs |
| 80 | A ₁₈ | I | Address Inputs |
| 63, 62, 59, 58, 57, 56, 53, 52 68, 69, 72, 73, 74, 75, 78, 79 13, 12, 9, 8, 7, 6, 3, 2 18, 19, 22, 23, 24, 25, 28, 29 | DQA ₁ DQA ₈ DQB ₁ DQB ₈ DQC ₁ DQC ₈ DQD ₁ DQD ₈ | I/O | Data Input and Output pins (x32, x36 Version) |
| 51, 80, 1, 30 | DQA ₉ , DQB ₉ , DQC ₉ , DQD ₉ | I/O | Data Input and Output pins |
| 51, 80, 1, 30 | NC | | No Connect (x32 Version) |
| 58, 59, 62, 63, 68, 69, 72, 73, 74 8, 9, 12, 13, 18, 19, 22, 23, 24 | DQA ₁ DQA ₉ DQB ₁ DQB ₉ | I/O | Data Input and Output pins |
| 51, 52, 53, 56, 57 75, 78, 79, 1, 2, 3, 6, 7 25, 28, 29, 30 | NC | | No Connect |
| 87 | BW | I | Byte Write Writes all enabled bytes; active low |
| 93, 94 | BA, BB | I | Byte Write Enable for DQA, DQB Data I/Os; active low |
| 95, 96 | BC, BD | I | Byte Write Enable for DQC, DQD Data I/Os; active low (x32, x36 Version) |
| 95, 96 | NC | | No Connect (x18 Version) |
| 89 | CK | I | Clock Input Signal; active high |
| 88 | GW | I | Global Write Enable Writes all bytes; active low |
| 98, 92 | E ₁ , E ₃ | I | Chip Enable; active low |
| 97 | E ₂ | I | Chip Enable; active high |
| 86 | G | I | Output Enable; active low |
| 83 | ADV | I | Burst address counter advance enable; active low |
| 84, 85 | ADSP, ADSC | I | Address Strobe (Processor, Cache Controller); active low |
| 64 | ZZ | I | Sleep mode control; active high |
| 14 | FT | I | Flow Through or Pipeline mode; active low |
| 31 | LBO | I | Linear Burst Order mode; active low |
| 15, 41, 65, 91 | V _{DD} | I | Core power supply |
| 5, 10, 17, 21, 26, 40, 55, 60, 67, 71, 76, 90 | V _{SS} | I | I/O and Core Ground |
| 4, 11, 20, 27, 54, 61, 70, 77 | V _{DDQ} | I | Output driver power supply |
| 16, 38, 39, 42, 66 | NC | | No Connect. |

GS880E32 Block Diagram



Note: Only x36 version shown for simplicity.

Mode Pin Functions

| Mode Name | Pin Name | State | Function |
|-------------------------|-------------------------|---------|----------------------------|
| Burst Order Control | $\overline{\text{LBO}}$ | L | Linear Burst |
| | | H or NC | Interleaved Burst |
| Output Register Control | $\overline{\text{FT}}$ | L | Flow Through |
| | | H or NC | Pipeline |
| Power Down Control | ZZ | L or NC | Active |
| | | H | Standby, $I_{DD} = I_{SB}$ |

Note:

There are pull-up devices on the $\overline{\text{LBO}}$ and $\overline{\text{FT}}$ pins and a pull down device on the ZZ pin, so those input pins can be unconnected and the chip will operate in the default states as specified in the above table.

Burst Counter Sequences

Linear Burst Sequence

| | A[1:0] | A[1:0] | A[1:0] | A[1:0] |
|-------------|--------|--------|--------|--------|
| 1st address | 00 | 01 | 10 | 11 |
| 2nd address | 01 | 10 | 11 | 00 |
| 3rd address | 10 | 11 | 00 | 01 |
| 4th address | 11 | 00 | 01 | 10 |

Note: The burst counter wraps to initial state on the 5th clock.

Interleaved Burst Sequence

| | A[1:0] | A[1:0] | A[1:0] | A[1:0] |
|-------------|--------|--------|--------|--------|
| 1st address | 00 | 01 | 10 | 11 |
| 2nd address | 01 | 00 | 11 | 10 |
| 3rd address | 10 | 11 | 00 | 01 |
| 4th address | 11 | 10 | 01 | 00 |

Note: The burst counter wraps to initial state on the 5th clock.

BPR 1999.05.18

Byte Write Truth Table

| Function | $\overline{\text{GW}}$ | $\overline{\text{BW}}$ | $\overline{\text{B}}_A$ | $\overline{\text{B}}_B$ | $\overline{\text{B}}_C$ | $\overline{\text{B}}_D$ | Notes |
|-----------------|------------------------|------------------------|-------------------------|-------------------------|-------------------------|-------------------------|---------|
| Read | H | H | X | X | X | X | 1 |
| Read | H | L | H | H | H | H | 1 |
| Write byte a | H | L | L | H | H | H | 2, 3 |
| Write byte b | H | L | H | L | H | H | 2, 3 |
| Write byte c | H | L | H | H | L | H | 2, 3, 4 |
| Write byte d | H | L | H | H | H | L | 2, 3, 4 |
| Write all bytes | H | L | L | L | L | L | 2, 3, 4 |
| Write all bytes | L | X | X | X | X | X | |

Notes:

- All byte outputs are active in read cycles regardless of the state of Byte Write Enable inputs.
- Byte Write Enable inputs $\overline{\text{B}}_A$, $\overline{\text{B}}_B$, $\overline{\text{B}}_C$, and/or $\overline{\text{B}}_D$ may be used in any combination with $\overline{\text{BW}}$ to write single or multiple bytes.
- All byte I/Os remain High-Z during all write operations regardless of the state of Byte Write Enable inputs.
- Bytes c and d are only available on the x32 and x36 versions.

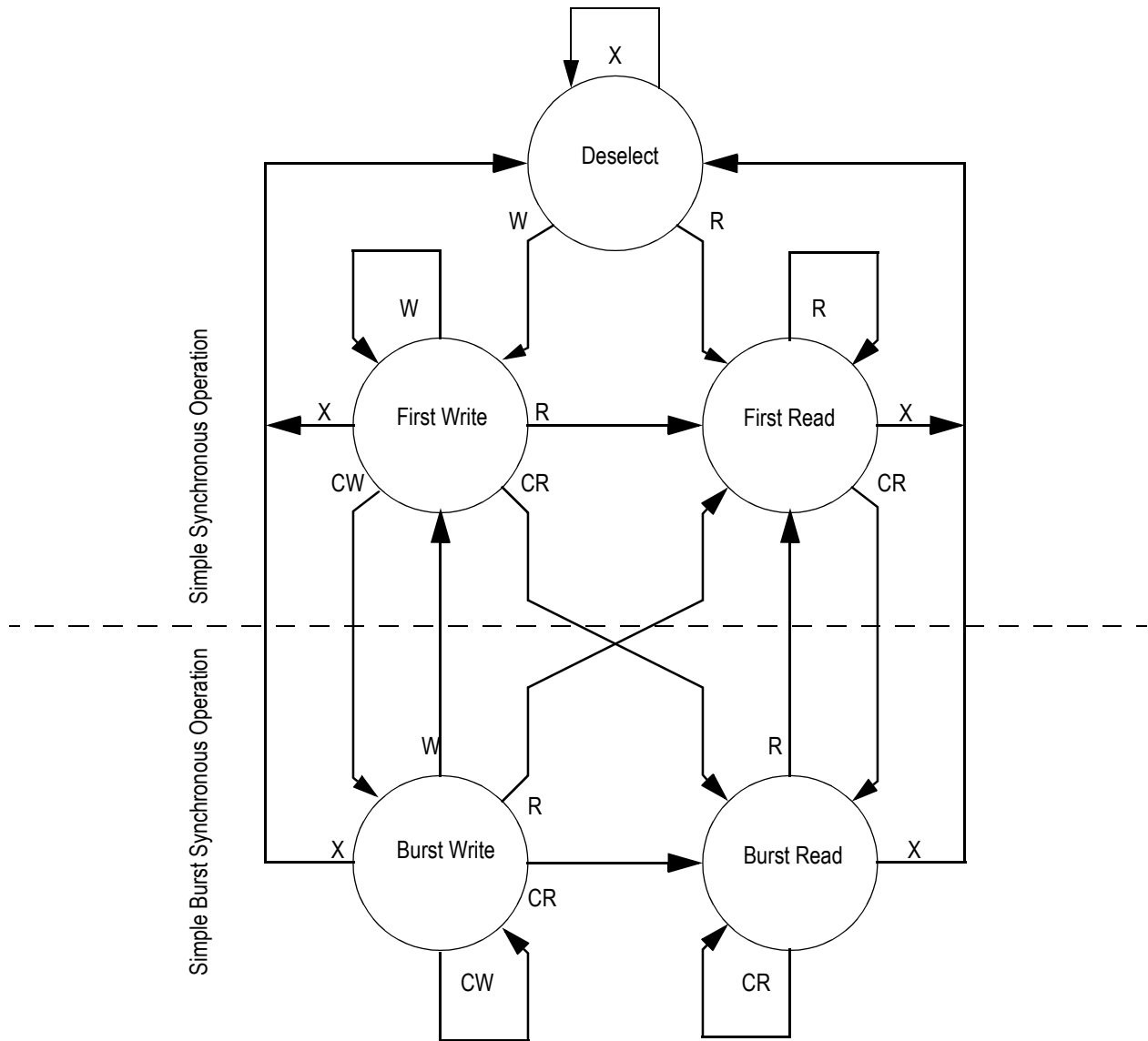
Synchronous Truth Table

| Operation | Address Used | State Diagram Key ⁵ | $\overline{E1}$ | $E2^2$ (x36only) | \overline{ADSP} | \overline{ADSC} | \overline{ADV} | W^3 | DQ^4 |
|------------------------------------|-----------------|--------------------------------|-----------------|---------------------|-------------------|-------------------|------------------|----------|---------------|
| Deselect Cycle, Power Down | None | X | H | X | X | L | X | X | High-Z |
| Deselect Cycle, Power Down | None | X | L | F | L | X | X | X | High-Z |
| Deselect Cycle, Power Down | None | X | L | F | H | L | X | X | High-Z |
| Read Cycle, Begin Burst | External | R | L | T | L | X | X | X | Q |
| Read Cycle, Begin Burst | External | R | L | T | H | L | X | F | Q |
| Write Cycle, Begin Burst | External | W | L | T | H | L | X | T | D |
| <i>Read Cycle, Continue Burst</i> | <i>Next</i> | <i>CR</i> | <i>X</i> | <i>X</i> | <i>H</i> | <i>H</i> | <i>L</i> | <i>F</i> | <i>Q</i> |
| Read Cycle, Continue Burst | Next | CR | H | X | X | H | L | F | Q |
| <i>Write Cycle, Continue Burst</i> | <i>Next</i> | <i>CW</i> | <i>X</i> | <i>X</i> | <i>H</i> | <i>H</i> | <i>L</i> | <i>T</i> | <i>D</i> |
| Write Cycle, Continue Burst | Next | CW | H | X | X | H | L | T | D |
| Read Cycle, Suspend Burst | Current | | X | X | H | H | H | F | Q |
| Read Cycle, Suspend Burst | Current | | H | X | X | H | H | F | Q |
| Write Cycle, Suspend Burst | Current | | X | X | H | H | H | T | D |
| Write Cycle, Suspend Burst | Current | | H | X | X | H | H | T | D |

Notes:

- X = Don't Care, H = High, L = Low.
- For x36 Version, E = T (True) if $E2 = 1$ and $\overline{E3} = 0$; E = F (False) if $E2 = 0$ or $\overline{E3} = 1$.
- $\overline{W} = T$ (True) and F (False) is defined in the Byte Write Truth Table preceding.
- \overline{G} is an asynchronous input. \overline{G} can be driven high at any time to disable active output drivers. \overline{G} low can only enable active drivers (shown as Q in the Truth Table above).
- All input combinations shown above are tested and supported. Input combinations shown in gray boxes need not be used to accomplish basic synchronous or synchronous burst operations and may be avoided for simplicity.
- Tying \overline{ADSP} high and \overline{ADSC} low allows simple non-burst synchronous operations. See **BOLD** items above.
- Tying \overline{ADSP} high and \overline{ADV} low while using \overline{ADSC} to load new addresses allows simple burst operations. See *ITALIC* items above.

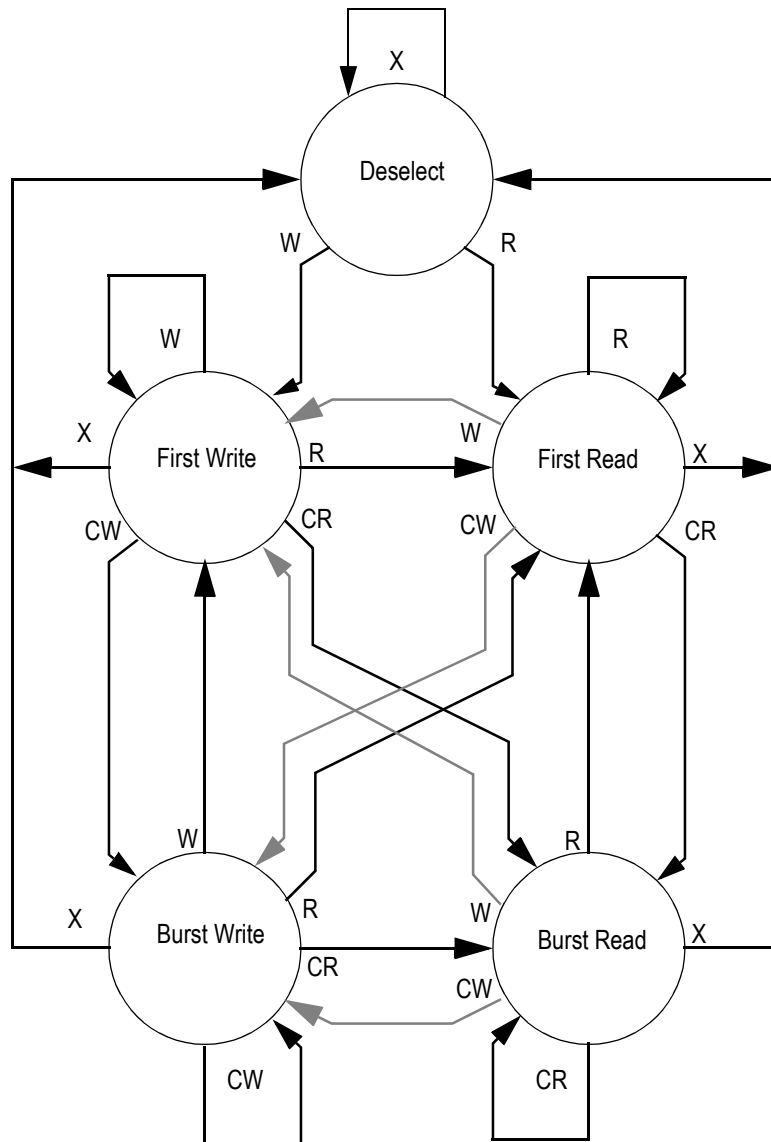
Simplified State Diagram



Notes:

1. The diagram shows only supported (tested) synchronous state transitions. The diagram presumes \overline{G} is tied low.
2. The upper portion of the diagram assumes active use of only the Enable ($\overline{E1}$, $\overline{E2}$, and $\overline{E3}$) and Write ($\overline{B_A}$, $\overline{B_B}$, $\overline{B_C}$, $\overline{B_D}$, $\overline{B_W}$, and $\overline{G_W}$) control inputs, and that \overline{ADSP} is tied high and \overline{ADSC} is tied low.
3. The upper and lower portions of the diagram together assume active use of only the Enable, Write, and \overline{ADSC} control inputs, and assumes \overline{ADSP} is tied high and \overline{ADV} is tied low.

Simplified State Diagram with \overline{G}



Notes:

1. The diagram shows supported (tested) synchronous state transitions plus supported transitions that depend upon the use of \overline{G} .
2. Use of Dummy Reads (Read Cycles with \overline{G} High) may be used to make the transition from Read cycles to Write cycles without passing through a Deselect cycle. Dummy Read cycles increment the address counter just like normal Read cycles.
3. Transitions shown in grey tone assume \overline{G} has been pulsed high long enough to turn the RAM's drivers off and for incoming data to meet Data Input Set Up Time.

Absolute Maximum Ratings

(All voltages reference to V_{SS})

| Symbol | Description | Value | Unit |
|------------|-------------------------------|---|-------------|
| V_{DD} | Voltage on V_{DD} Pins | 0.5 to 4.6 | V |
| V_{DDQ} | Voltage in V_{DDQ} Pins | 0.5 to V_{DD} | V |
| V_{CK} | Voltage on Clock Input Pin | 0.5 to 6 | V |
| $V_{I/O}$ | Voltage on I/O Pins | 0.5 to $V_{DDQ} + 0.5$ (≤ 4.6 V max.) | V |
| V_{IN} | Voltage on Other Input Pins | 0.5 to $V_{DD} + 0.5$ (≤ 4.6 V max.) | V |
| I_{IN} | Input Current on Any Pin | +/- 20 | mA |
| I_{OUT} | Output Current on Any I/O Pin | +/- 20 | mA |
| P_D | Package Power Dissipation | 1.5 | W |
| T_{STG} | Storage Temperature | 55 to 125 | $^{\circ}C$ |
| T_{BIAS} | Temperature Under Bias | 55 to 125 | $^{\circ}C$ |

Note:

Permanent damage to the device may occur if the Absolute Maximum Ratings are exceeded. Operation should be restricted to Recommended Operating Conditions. Exposure to conditions exceeding the Absolute Maximum Ratings, for an extended period of time, may affect reliability of this component.

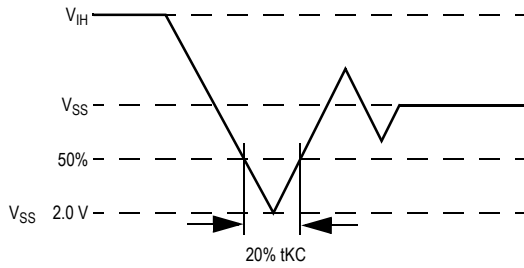
Recommended Operating Conditions

| Parameter | Symbol | Min. | Typ. | Max. | Unit | Notes |
|---|-----------|-------|------|----------------|-------------|-------|
| Supply Voltage | V_{DD} | 3.135 | 3.3 | 3.6 | V | |
| I/O Supply Voltage | V_{DDQ} | 2.375 | 2.5 | V_{DD} | V | 1 |
| Input High Voltage | V_{IH} | 1.7 | | $V_{DD} + 0.3$ | V | 2 |
| Input Low Voltage | V_{IL} | 0.3 | | 0.8 | V | 2 |
| Ambient Temperature (Commercial Range Versions) | T_A | 0 | 25 | 70 | $^{\circ}C$ | 3 |
| Ambient Temperature (Industrial Range Versions) | T_A | 40 | 25 | 85 | $^{\circ}C$ | 3 |

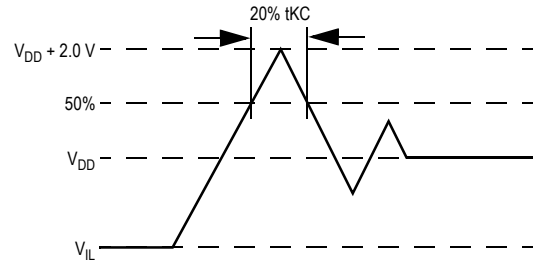
Notes:

- Unless otherwise noted, all performance specifications quoted are evaluated for worst case at both $2.75\text{ V} \leq V_{DDQ} \leq 2.375\text{ V}$ (i.e., 2.5 V I/O) and $3.6\text{ V} \leq V_{DDQ} \leq 3.135\text{ V}$ (i.e., 3.3 V I/O), and quoted at whichever condition is worst case.
- This device features input buffers compatible with both 3.3 V and 2.5 V I/O drivers.
- Most speed grades and configurations of this device are offered in both Commercial and Industrial Temperature ranges. The part number of Industrial Temperature Range versions end the character I. Unless otherwise noted, all performance specifications quoted are evaluated for worst case in the temperature range marked on the device.
- Input Under/overshoot voltage must be $-2\text{ V} > V_i < V_{DD} + 2\text{ V}$ with a pulse width not to exceed 20% tKC.

Undershoot Measurement and Timing



Overshoot Measurement and Timing



Capacitance

($T_A = 25^\circ\text{C}$, $f = 1\text{ MHz}$, $V_{DD} = 3.3\text{ V}$)

| Parameter | Symbol | Test conditions | Typ. | Max. | Unit |
|--------------------------|-----------|------------------------|------|------|------|
| Input Capacitance | C_{IN} | $V_{IN} = 0\text{ V}$ | 4 | 5 | pF |
| Input/Output Capacitance | $C_{I/O}$ | $V_{OUT} = 0\text{ V}$ | 6 | 7 | pF |

Note: These parameters are sample tested.

Package Thermal Characteristics

| Rating | Layer Board | Symbol | Max | Unit | Notes |
|----------------------------------|-------------|-----------------|-----|--------------------|-------|
| Junction to Ambient (at 200 lfm) | single | $R_{\theta JA}$ | 40 | $^\circ\text{C/W}$ | 1,2 |
| Junction to Ambient (at 200 lfm) | four | $R_{\theta JA}$ | 24 | $^\circ\text{C/W}$ | 1,2 |
| Junction to Case (TOP) | | $R_{\theta JC}$ | 9 | $^\circ\text{C/W}$ | 3 |

Notes:

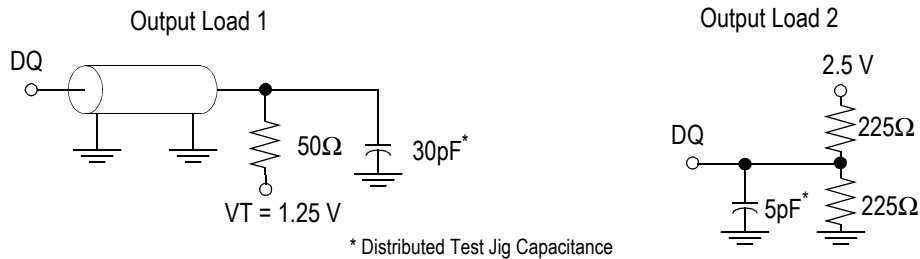
- Junction temperature is a function of SRAM power dissipation, package thermal resistance, mounting board temperature, ambient. Temperature air flow, board density, and PCB thermal resistance.
- SCMI G-38-87
- Average thermal resistance between die and top surface, MIL SPEC-883, Method 1012.1

AC Test Conditions

| Parameter | Conditions |
|------------------------|-----------------------|
| Input high level | 2.3 V |
| Input low level | 0.2 V |
| Input slew rate | 1 V/ns |
| Input reference level | 1.25 V |
| Output reference level | 1.25 V |
| Output load | Fig. 1 & 2 |

Notes:

1. Include scope and jig capacitance.
2. Test conditions as specified with output loading as shown in **Fig. 1** unless otherwise noted.
3. Output Load 2 for t_{LZ} , t_{HZ} , t_{OLZ} and t_{OHZ}
4. Device is deselected as defined by the Truth Table.



DC Electrical Characteristics

| Parameter | Symbol | Test Conditions | Min | Max |
|--|------------|---|--------------------------------------|--------------------------------------|
| Input Leakage Current (except mode pins) | I_{IL} | $V_{IN} = 0 \text{ to } V_{DD}$ | 1 μA | 1 μA |
| ZZ Input Current | I_{INZZ} | $V_{DD} \geq V_{IN} \geq V_{IH}$ $0 \text{ V} \leq V_{IN} \leq V_{IH}$ | 1 μA 1 μA | 1 μA 300 μA |
| Mode Pin Input Current | I_{INM} | $V_{DD} \geq V_{IN} \geq V_{IL}$ $0 \text{ V} \leq V_{IN} \leq V_{IL}$ | 300 μA 1 μA | 1 μA 1 μA |
| Output Leakage Current | I_{OL} | Output Disable, $V_{OUT} = 0 \text{ to } V_{DD}$ | 1 μA | 1 μA |
| Output High Voltage | V_{OH} | $I_{OH} = 8 \text{ mA}$, $V_{DDQ} = 2.375 \text{ V}$ | 1.7 V | |
| Output High Voltage | V_{OH} | $I_{OH} = 8 \text{ mA}$, $V_{DDQ} = 3.135 \text{ V}$ | 2.4 V | |
| Output Low Voltage | V_{OL} | $I_{OL} = 8 \text{ mA}$ | | 0.4 V |

Operating Currents

| Parameter | Test Conditions | Symbol | -11 | | -11.5 | | -100 | | -80 | | -66 | | Unit |
|-------------------|--|--------------------|-----------|------------|-----------|------------|-----------|------------|-----------|------------|-----------|------------|------|
| | | | 0 to 70°C | 40 to 85°C | 0 to 70°C | 40 to 85°C | 0 to 70°C | 40 to 85°C | 0 to 70°C | 40 to 85°C | 0 to 70°C | 40 to 85°C | |
| Operating Current | Device Selected; All other inputs $\geq V_{IH}$ or $\leq V_{IL}$ Output open | I_{DD} Pipeline | 225 | 235 | 225 | 235 | 225 | 235 | 200 | 210 | 185 | 195 | mA |
| | | I_{DD} Flow-Thru | 180 | 190 | 180 | 190 | 180 | 190 | 175 | 185 | 165 | 175 | mA |
| Standby Current | $ZZ \geq V_{DD} - 0.2V$ | I_{SB} Pipeline | 30 | 40 | 30 | 40 | 30 | 40 | 30 | 40 | 30 | 40 | mA |
| | | I_{SB} Flow-Thru | 30 | 40 | 30 | 40 | 30 | 40 | 30 | 40 | 30 | 40 | mA |
| Deselect Current | Device Deselected; All other inputs $\geq V_{IH}$ or $\leq V_{IL}$ | I_{DD} Pipeline | 80 | 90 | 80 | 90 | 80 | 90 | 70 | 80 | 60 | 70 | mA |
| | | I_{DD} Flow-Thru | 65 | 75 | 65 | 75 | 65 | 75 | 55 | 65 | 50 | 60 | mA |

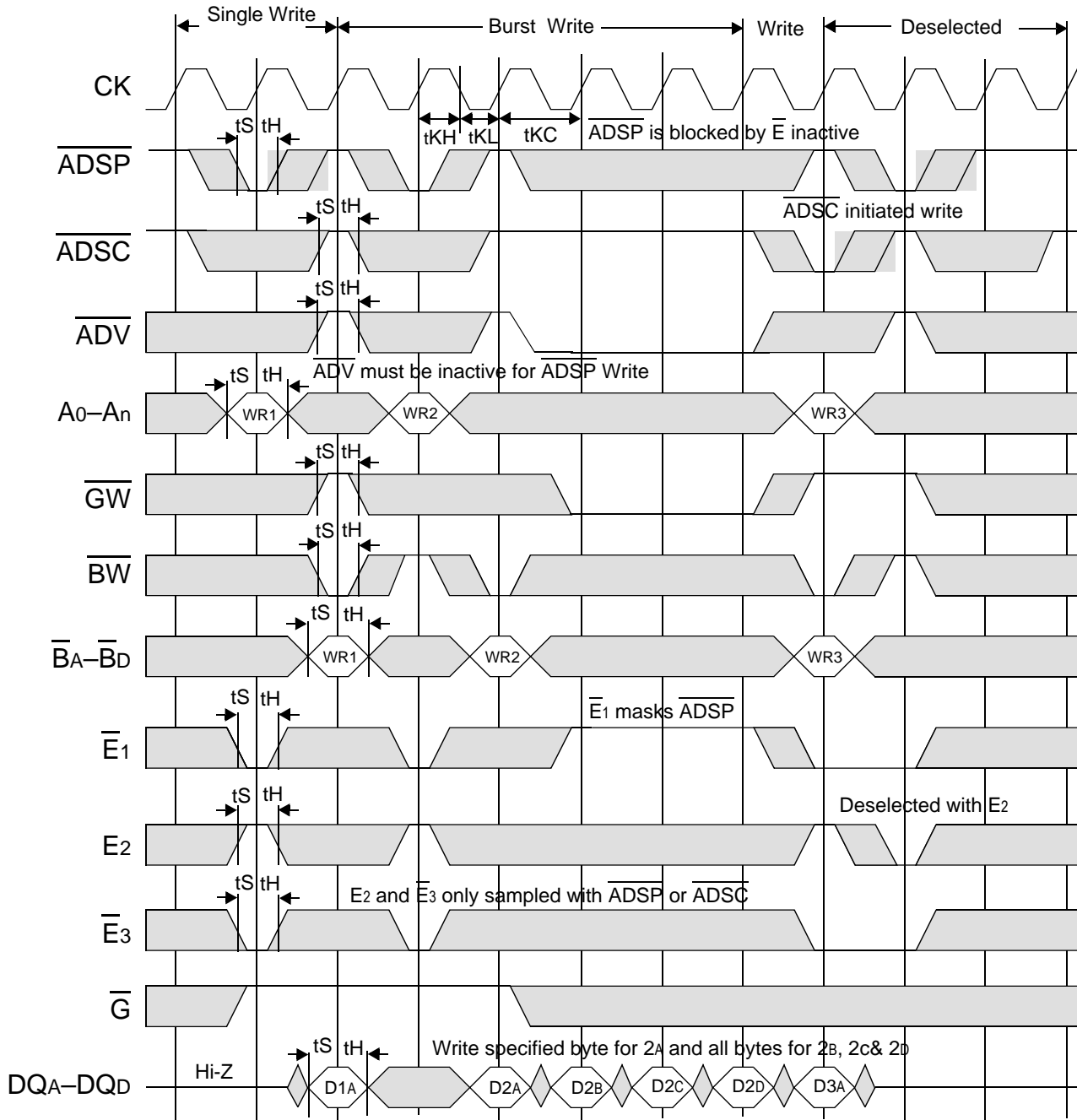
AC Electrical Characteristics

| | Parameter | Symbol | -11 | | -11.5 | | -100 | | -80 | | -66 | | Unit |
|-----------|-------------------------------|-------------------------------|------|------|-------|------|------|------|------|------|-----|-----|------|
| | | | Min | Max | Min | Max | Min | Max | Min | Max | Min | Max | |
| Pipeline | Clock Cycle Time | t _{KC} | 10 | | 10 | | 10 | | 12.5 | | 15 | | ns |
| | Clock to Output Valid | t _{KQ} | | 4.0 | | 4.0 | | 4.0 | | 4.5 | | 5 | ns |
| | Clock to Output Invalid | t _{KQX} | 1.5 | | 1.5 | | 1.5 | | 1.5 | | 1.5 | | ns |
| | Clock to Output in Low-Z | t _{LZ} ¹ | 1.5 | | 1.5 | | 1.5 | | 1.5 | | 1.5 | | ns |
| Flow-Thru | Clock Cycle Time | t _{KC} | 15.0 | | 15.0 | | 15.0 | | 15.0 | | 20 | | ns |
| | Clock to Output Valid | t _{KQ} | | 11.0 | | 11.5 | | 12.0 | | 14.0 | | 18 | ns |
| | Clock to Output Invalid | t _{KQX} | 3.0 | | 3.0 | | 3.0 | | 3.0 | | 3.0 | | ns |
| | Clock to Output in Low-Z | t _{LZ} ¹ | 3.0 | | 3.0 | | 3.0 | | 3.0 | | 3.0 | | ns |
| | Clock HIGH Time | t _{KH} | 1.7 | | 1.7 | | 2 | | 2 | | 2.3 | | ns |
| | Clock LOW Time | t _{KL} | 2 | | 2 | | 2.2 | | 2.2 | | 2.5 | | ns |
| | Clock to Output in High-Z | t _{HZ} ¹ | 1.5 | 4.0 | 1.5 | 4.2 | 1.5 | 4.5 | 1.5 | 4.5 | 1.5 | 4.8 | ns |
| | G to Output Valid | t _{OE} | | 4.0 | | 4.2 | | 4.5 | | 4.5 | | 4.8 | ns |
| | \bar{G} to output in Low-Z | t _{OLZ} ¹ | 0 | | 0 | | 0 | | 0 | | 0 | | ns |
| | \bar{G} to output in High-Z | t _{OHz} ¹ | | 4.0 | | 4.2 | | 4.5 | | 4.5 | | 4.8 | ns |
| | Setup time | t _S | 1.5 | | 2.0 | | 2.0 | | 2.0 | | 2.0 | | ns |
| | Hold time | t _H | 0.5 | | 0.5 | | 0.5 | | 0.5 | | 0.5 | | ns |
| | ZZ setup time | t _{ZZS} ² | 5 | | 5 | | 5 | | 5 | | 5 | | ns |
| | ZZ hold time | t _{ZZH} ² | 1 | | 1 | | 1 | | 1 | | 1 | | ns |
| | ZZ recovery | t _{ZZR} | 20 | | 20 | | 20 | | 20 | | 20 | | ns |

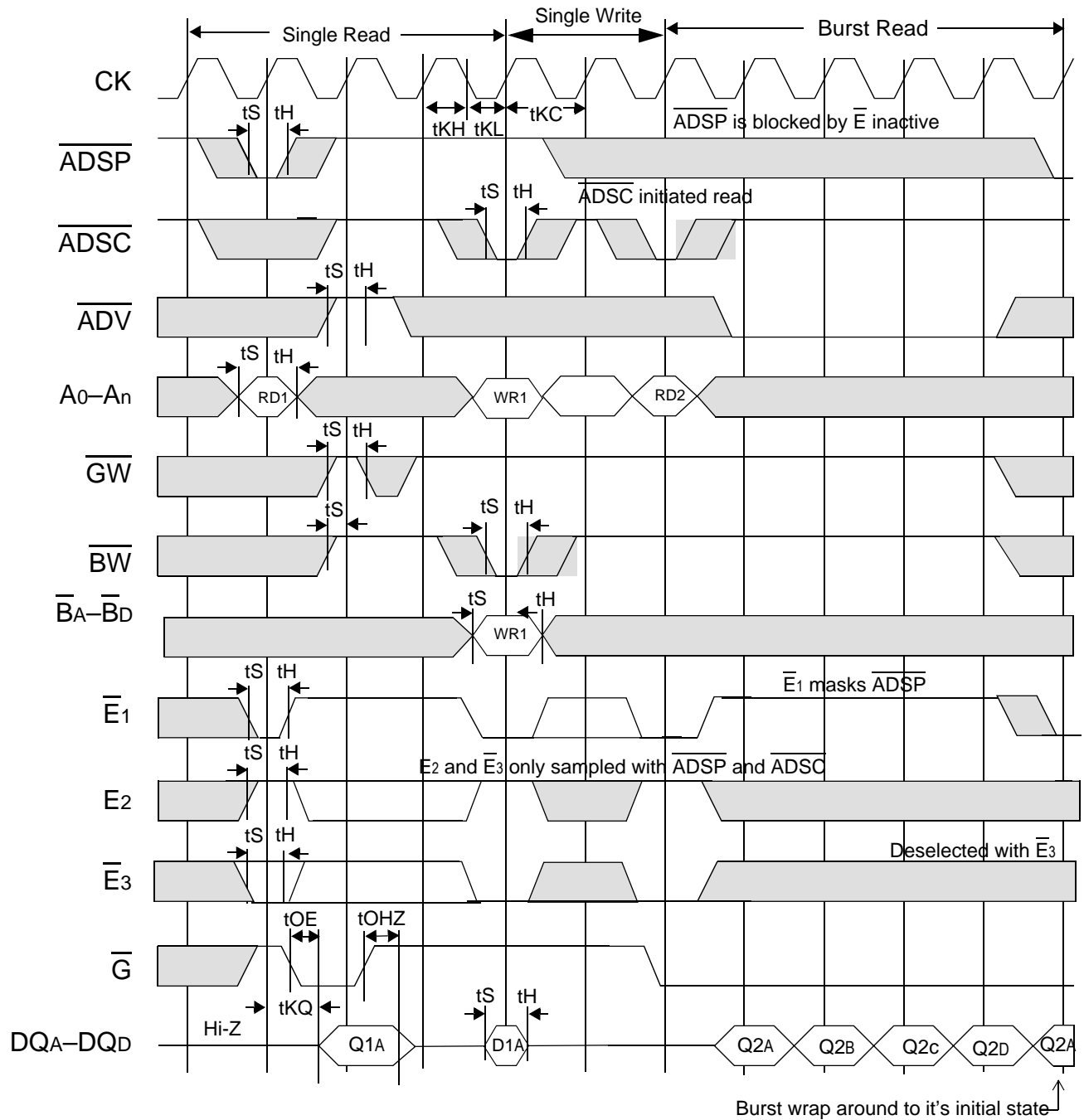
Notes:

1. These parameters are sampled and are not 100% tested.
2. ZZ is an asynchronous signal. However, in order to be recognized on any given clock cycle, ZZ must meet the specified setup and hold times as specified above.

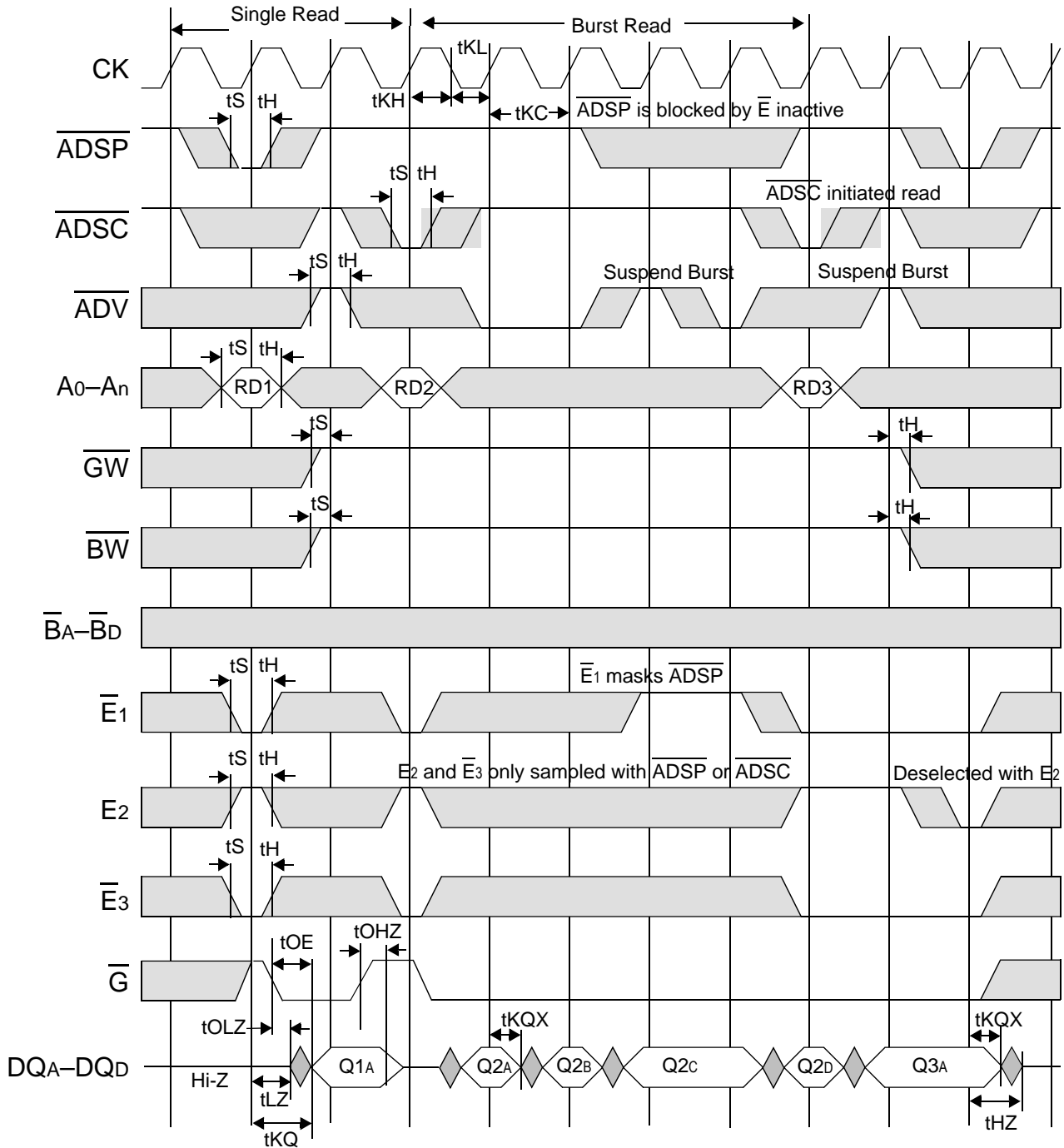
Write Cycle Timing



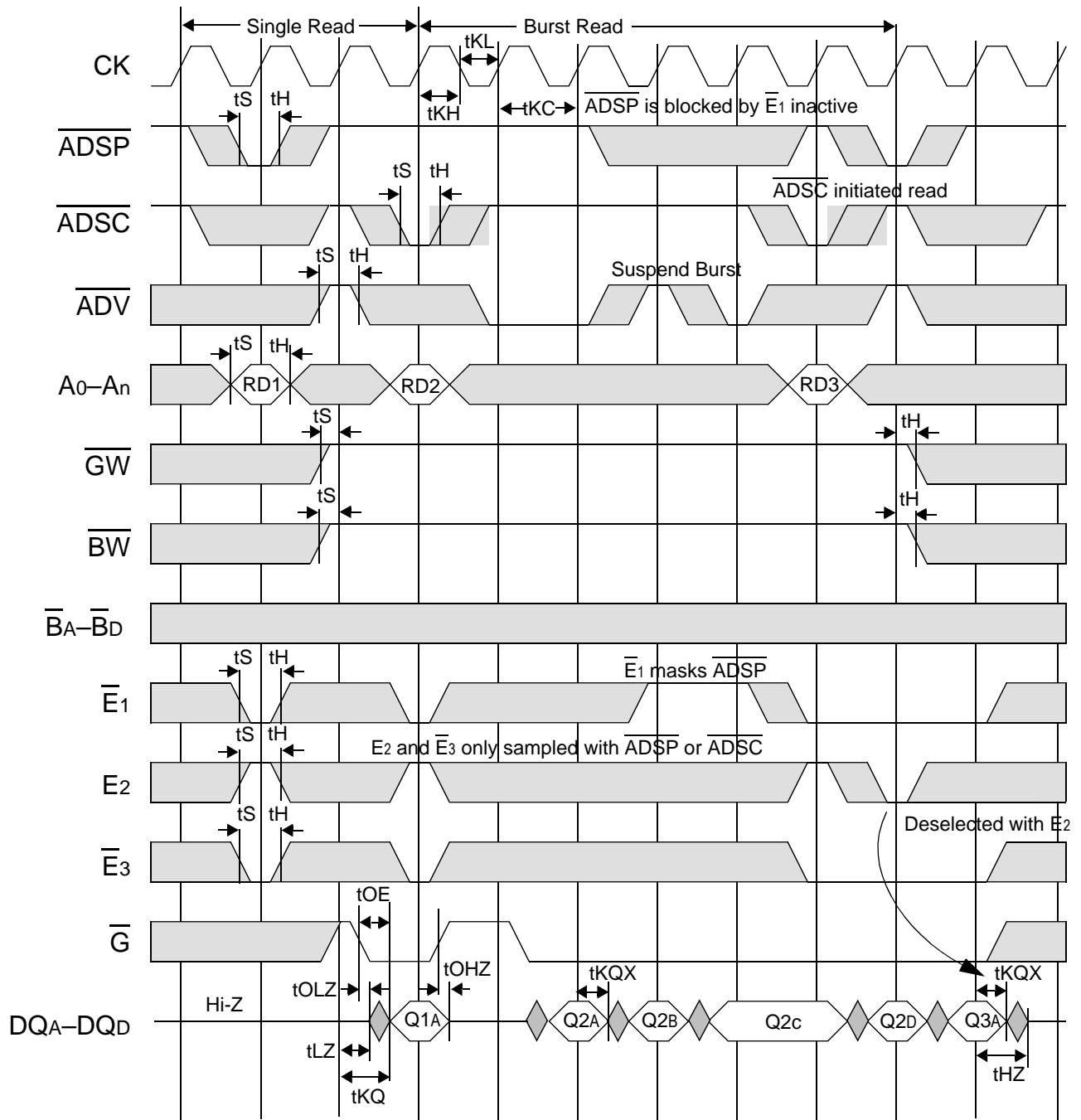
Flow Through Read-Write Cycle Timing



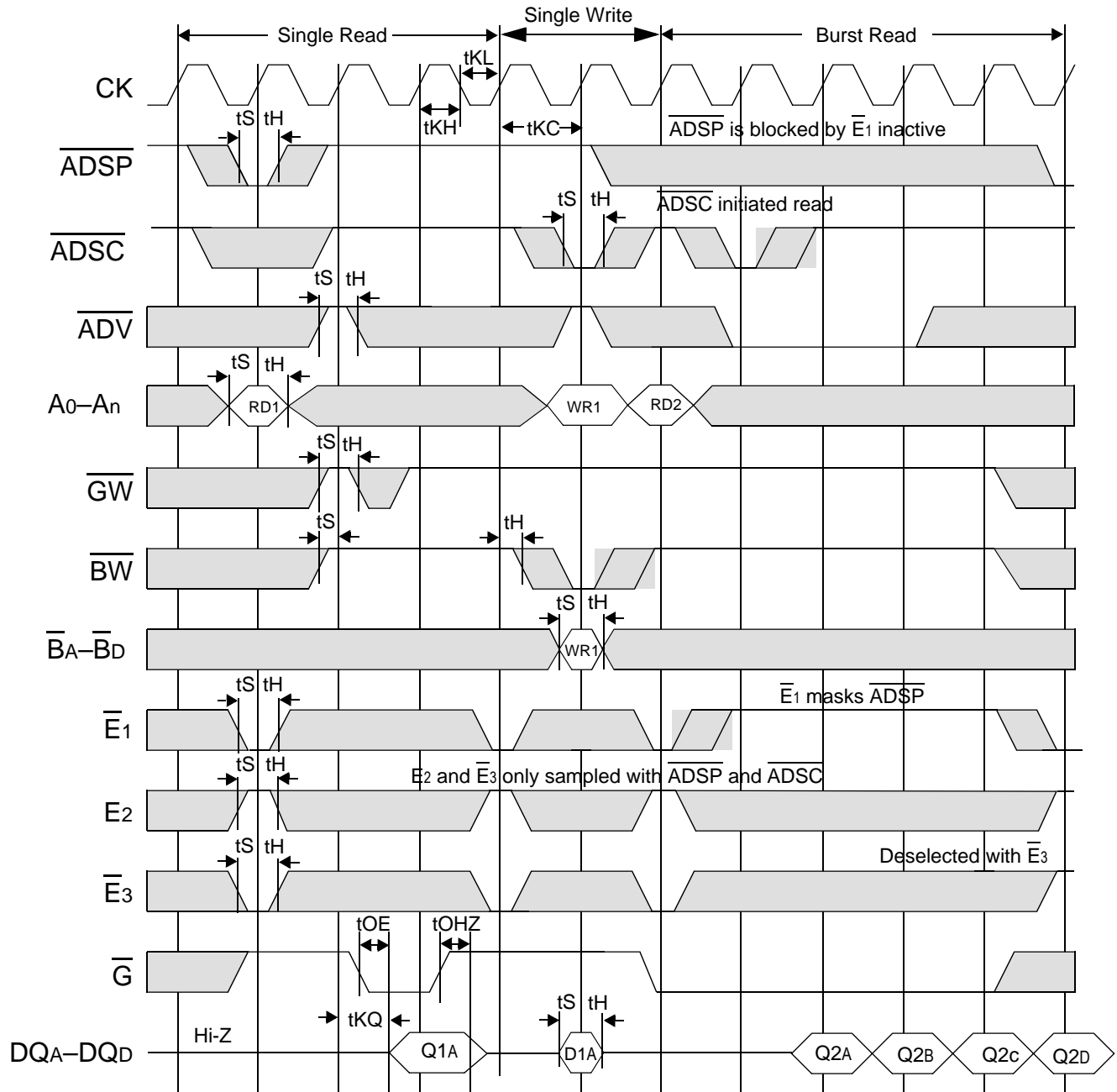
Flow Through Read Cycle Timing



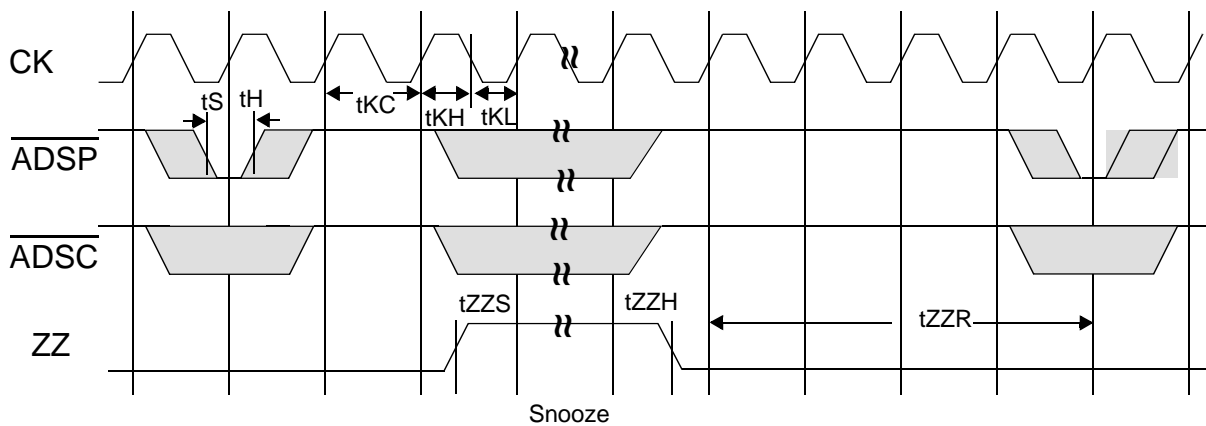
Pipelined DCD Read Cycle Timing



Pipelined DCD Read-Write Cycle Timing



Sleep Mode Timing Diagram

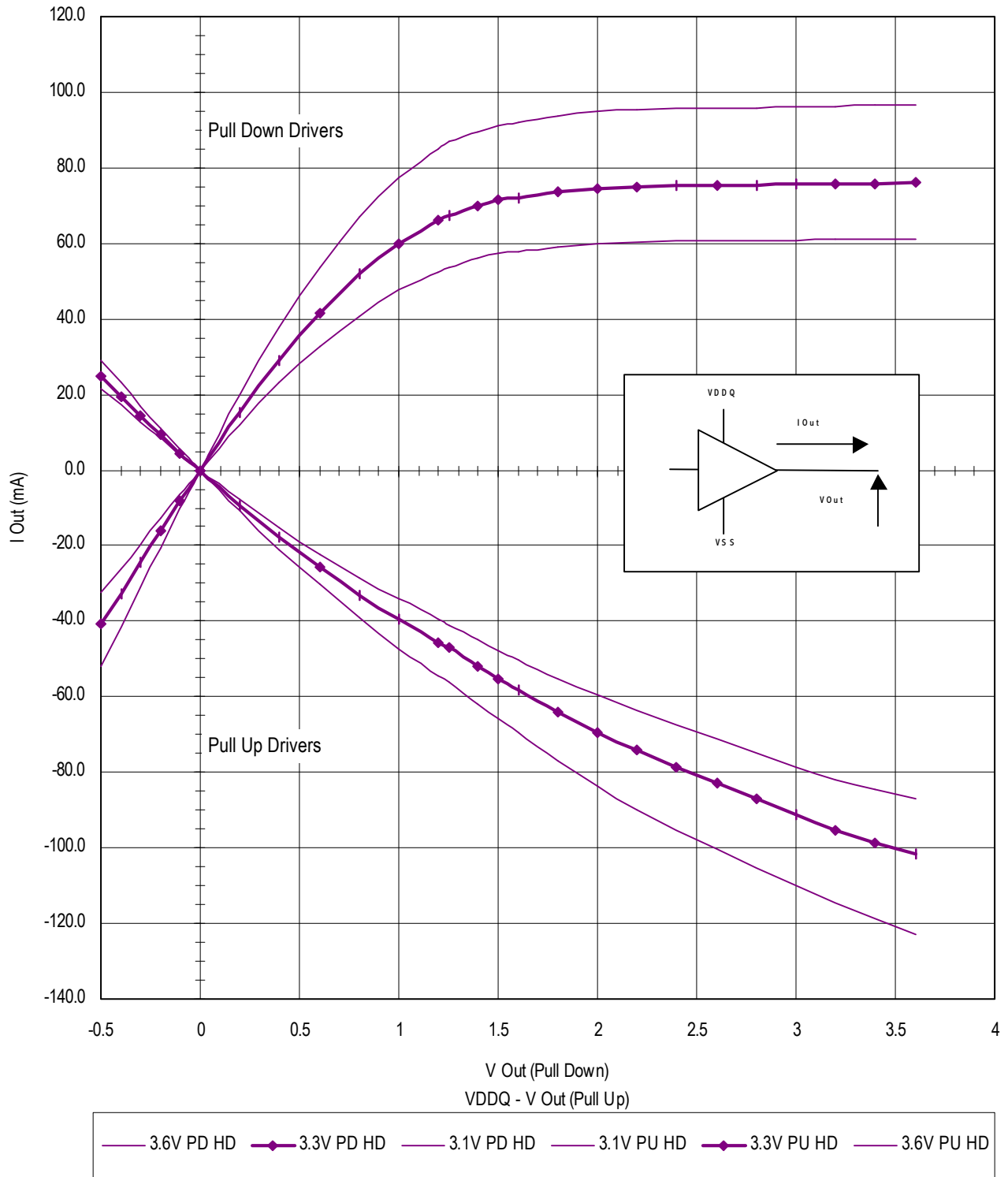


Application Tips

Single and Dual Cycle Deselect

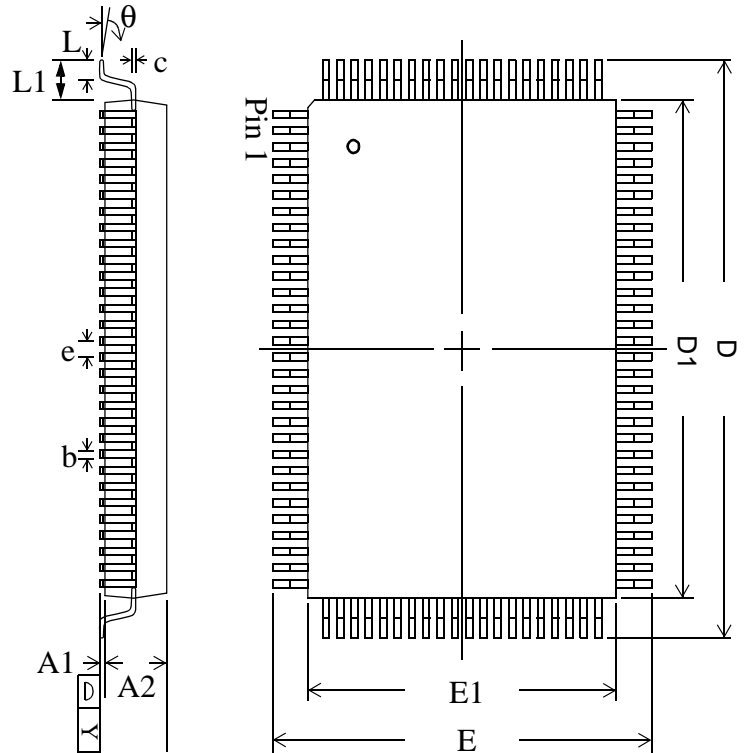
SCD devices force the use of "dummy read cycles" (read cycles that are launched normally but that are ended with the output drivers inactive) in a fully synchronous environment. Dummy read cycles waste performance but their use usually assures there will be no bus contention in transitions from reads to writes or between banks of RAMs. DCD SRAMs do not waste bandwidth on dummy cycles and are logically simpler to manage in a multiple bank application (wait states need not be inserted at bank address boundary crossings) but greater care must be exercised to avoid excessive bus contention.

Output Driver Characteristics



TQFP Package Drawing

| Symbol | Description | Min. | Nom. | Max |
|----------|--------------------|------|------|------|
| A1 | Standoff | 0.05 | 0.10 | 0.15 |
| A2 | Body Thickness | 1.35 | 1.40 | 1.45 |
| b | Lead Width | 0.20 | 0.30 | 0.40 |
| c | Lead Thickness | 0.09 | | 0.20 |
| D | Terminal Dimension | 21.9 | 22.0 | 22.1 |
| D1 | Package Body | 19.9 | 20.0 | 20.1 |
| E | Terminal Dimension | 15.9 | 16.0 | 16.1 |
| E1 | Package Body | 13.9 | 14.0 | 14.1 |
| e | Lead Pitch | | 0.65 | |
| L | Foot Length | 0.45 | 0.60 | 0.75 |
| L1 | Lead Length | | 1.00 | |
| Y | Coplanarity | | | 0.10 |
| θ | Lead Angle | 0° | | 7° |



Notes:

1. All dimensions are in millimeters (mm).
2. Package width and length do not include mold protrusion.

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Ordering Information for GSI Synchronous Burst RAMs

| Org | Part Number ¹ | Type | Package | Speed ² (MHz/ns) | T _A ³ | Status |
|-----------|--------------------------|---------------------------|---------|--------------------------------|-----------------------------|--------|
| 514K x 18 | GS880E18T-11 | DCD Pipeline/Flow Through | TQFP | 100/11 | C | |
| 514K x 18 | GS880E18T-11.5 | DCD Pipeline/Flow Through | TQFP | 100/11.5 | C | |
| 514K x 18 | GS880E18T-100 | DCD Pipeline/Flow Through | TQFP | 100/12 | C | |
| 514K x 18 | GS880E18T-80 | DCD Pipeline/Flow Through | TQFP | 80/14 | C | |
| 514K x 18 | GS880E18T-66 | DCD Pipeline/Flow Through | TQFP | 66/18 | C | |
| 256K x 32 | GS880E32T-11 | DCD Pipeline/Flow Through | TQFP | 100/11 | C | |
| 256K x 32 | GS880E32T-11.5 | DCD Pipeline/Flow Through | TQFP | 100/11.5 | C | |
| 256K x 32 | GS880E32T-100 | DCD Pipeline/Flow Through | TQFP | 100/12 | C | |
| 256K x 32 | GS880E32T-80 | DCD Pipeline/Flow Through | TQFP | 80/14 | C | |
| 256K x 32 | GS880E32T-66 | DCD Pipeline/Flow Through | TQFP | 66/18 | C | |
| 256K x 36 | GS880E36T-11 | DCD Pipeline/Flow Through | TQFP | 100/11 | C | |
| 256K x 36 | GS880E36T-11.5 | DCD Pipeline/Flow Through | TQFP | 100/11.5 | C | |
| 256K x 36 | GS880E36T-100 | DCD Pipeline/Flow Through | TQFP | 100/12 | C | |
| 256K x 36 | GS880E36T-80 | DCD Pipeline/Flow Through | TQFP | 80/14 | C | |
| 256K x 36 | GS880E36T-66 | DCD Pipeline/Flow Through | TQFP | 66/18 | C | |
| 514K x 18 | GS880E18T-11I | DCD Pipeline/Flow Through | TQFP | 100/11 | I | |
| 514K x 18 | GS880E18T-11.5I | DCD Pipeline/Flow Through | TQFP | 100/11.5 | I | |
| 514K x 18 | GS880E18T-100I | DCD Pipeline/Flow Through | TQFP | 100/12 | I | |
| 514K x 18 | GS880E18T-80I | DCD Pipeline/Flow Through | TQFP | 80/14 | I | |
| 514K x 18 | GS880E18T-66I | DCD Pipeline/Flow Through | TQFP | 66/18 | I | |
| 256K x 32 | GS880E32T-11I | DCD Pipeline/Flow Through | TQFP | 100/11 | I | |
| 256K x 32 | GS880E32T-11.5I | DCD Pipeline/Flow Through | TQFP | 100/11.5 | I | |
| 256K x 32 | GS880E32T-100I | DCD Pipeline/Flow Through | TQFP | 100/12 | I | |
| 256K x 32 | GS880E32T-80I | DCD Pipeline/Flow Through | TQFP | 80/14 | I | |
| 256K x 32 | GS880E32T-66I | DCD Pipeline/Flow Through | TQFP | 66/18 | I | |
| 256K x 36 | GS880E36T-11I | DCD Pipeline/Flow Through | TQFP | 100/11 | I | |
| 256K x 36 | GS880E36T-11.5I | DCD Pipeline/Flow Through | TQFP | 100/11.5 | I | |
| 256K x 36 | GS880E36T-100I | DCD Pipeline/Flow Through | TQFP | 100/12 | I | |
| 256K x 36 | GS880E36T-80I | DCD Pipeline/Flow Through | TQFP | 80/14 | I | |
| 256K x 36 | GS880E36T-66I | DCD Pipeline/Flow Through | TQFP | 66/18 | I | |

Notes:

- Customers requiring delivery in Tape and Reel should add the character T to the end of the part number. Example: GS880E18TT.
- The speed column indicates the cycle frequency (MHz) of the device in Pipeline mode and the latency (ns) in Flow Through mode. Each device is Pipeline/Flow Through mode-selectable by the user.
- T_A = C = Commercial Temperature Range. T_A = I = Industrial Temperature Range.
- GSI offers other versions this type of device in many different configurations and with a variety of different features, only some of which are covered in this data sheet. See the GSI Technology web site (www.gsistechnology.com) for a complete listing of current offerings.

Revision History

| DS/Date Rev. Code: Old; New | Types of Changes Format or Content | Page; Revisions; Reason |
|--|---------------------------------------|---|
| GS880E18/32/36T Rev1.04h 5/1999; 1.05 9/1999l | Format/Typos | <ul style="list-style-type: none"> • Last Page/Fixed "GSGS.." in Ordering Information Note. • Formatted Pin Outs and Pin Description to new small caps. • Formatted Block diagrams to new small caps. • Formatted Timing Diagrams to new small caps. • Changed "Flow thru" to "Flow Through" in Timing Diagrams. • Package Diagram/Changed "Dimesion" to "Dimension". |
| | Content | <ul style="list-style-type: none"> • 5/Fixed pin description table to match pinouts. • Pin Description/Changed chip enables to match pins. • Pin Description/Changed pin 80 from NC to Address Input. • Pin Description/Rearranged Address Inputs to match order of Pinout • Package Diagram/Changed Dimension D Max from 20.1 to 22.1 |
| GS880E18/32/36T 1.05 11/ 1999 K880E18/32/36T 1.06 1/ 2000L | Content | <ul style="list-style-type: none"> • Changed Flow Through Read-Write Cycle Timing Diagram for accuracy. • Changed order of TQFP Address Inputs to match pinout. • Changed order of TQFP DATA Input and Output pins to match pinout. • New GSI Logo. |
| GS880E18/32/36T1.06 1/ 2000L; GS880E18/32/36T1.07 3/ 2000N; | Content | <ul style="list-style-type: none"> • Changed all speed bin information (headings, references, tables, ordering info..) to reflect 150 - 80Mhz |
| GS880E18/32/36T1.07 3/ 2000N; GS880E18/32/36T1.08 3/ 2000O; | Content | <ul style="list-style-type: none"> • Corrections to AC Electrical Characteristics Table - |
| GS880E18/32/36T1.08 3/ 2000O; 880E183236_r1_09 | Content/Format | <ul style="list-style-type: none"> • Removed 150 MHz speed bin • Changed 133 MHz and 117 MHz speed bins to 11 ns and 11.5 ns (100 MHz) numbers • Updated format to comply with Technical Publications standards |
| 880E18_r1_09; 880E18_r1_10 | Content | <ul style="list-style-type: none"> • Updated Capitanace table—removed Input row and changed Output row to I/O |
| 880E18_r1_10; 880E18_r1_11 | Content | <ul style="list-style-type: none"> • Corrected typo in AC Electrical Characteristics table |